

NPN General Purpose Amplifier

This device is designed for general purpose high voltage amplifiers and gas discharge display drivers.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	160	V
V _{CBO}	Collector-Base Voltage	180	V
V _{EBO}	Emitter-Base Voltage	6.0	V
lc	Collector Current - Continuous 600 mA		mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units
		2N5551	*MMBT5551	
P _D	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

NPN General Purpose Amplifier

(continued)

Electrical Characteristics TA = 25°C unless otherwise noted						
Symbol	Parameter	Test Conditions	Min	Max	Units	
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OFF CHA	RACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Sustaining Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	160		V	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	180		V	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	6.0		V	
I _{CBO}	Collector Cutoff Current	$V_{CB} = 120 \text{ V}, \text{ I}_{\text{E}} = 0,$		50	nA	
		$V_{CB} = 120 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$		50	μΑ	
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		50	nA	
h _{FE} V _{CE(sat)}	DC Current Gain Collector-Emitter Saturation Voltage	$I_{c} = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{c} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{c} = 50 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{c} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$	80 80 30	250 0.15	V	
CE(SAI)	5	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$		0.20	V	
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$ $I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$		1.0 1.0	V V	
	GNAL CHARACTERISTICS					
f _T	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	100	300	MHz	
C _{obo}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0,$ f = 1.0 MHz		6.0	pF	
C _{ibo}	Input Capacitance	$V_{BE} = 0.5 \text{ V}, I_C = 0,$ f = 1.0 MHz		20	pF	
h _{fe}	Small-Signal Current Gain	$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 1.0 kHz	50	250		
NF	Noise Figure	$I_c = 250 \mu$ A, V _{CE} = 5.0 V, R _s =1.0 kΩ, f=10 Hz to 15.7 kHz		8.0	dB	

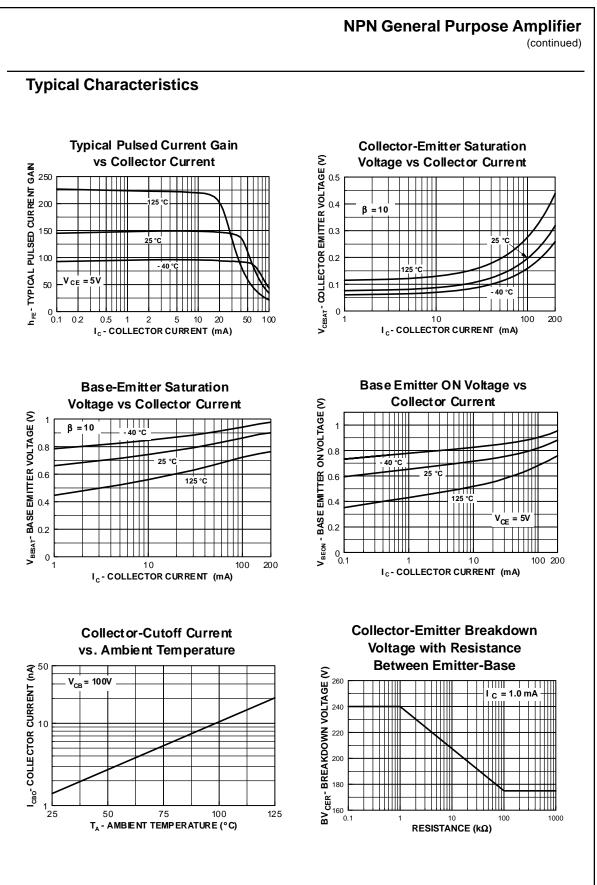
*Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%

Spice Model

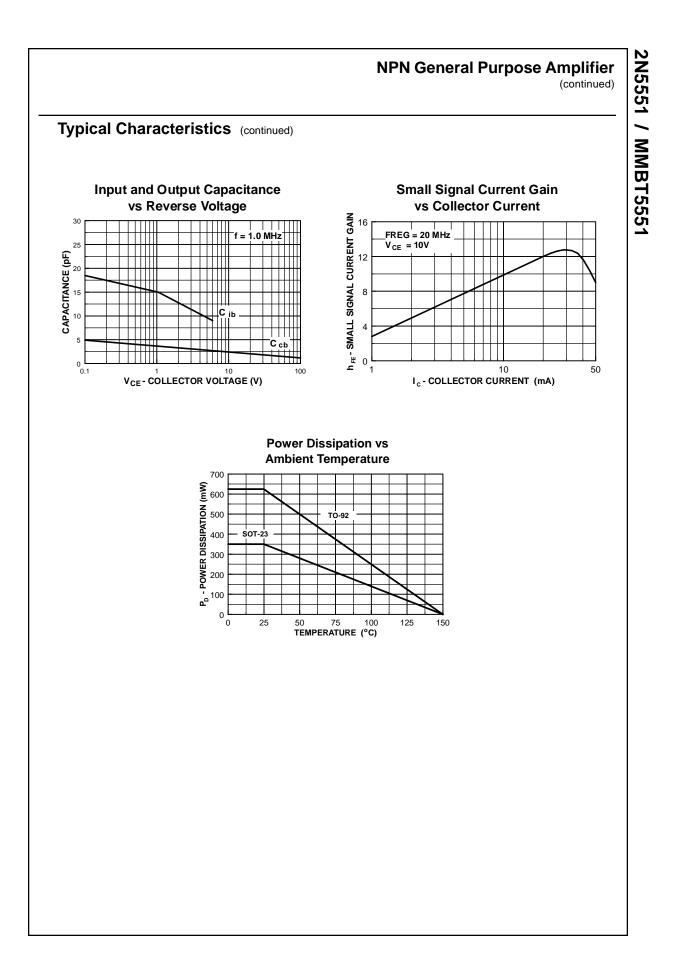
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NPN (Is=2.511f Xti=3 Eg=1.11 Vaf=100 Bf=242.6 Ne=1.249 Ise=2.511f Ikf=.3458 Xtb=1.5 Br=3.197 Nc=2 Isc=0 Ikr=0 Rc=1 Cjc=4.883p Mjc=.3047 Vjc=.75 Fc=.5 Cje=18.79p Mje=.3416 Vje=.75 Tr=1.202n Tf=560p Itf=50m Vtf=5 Xtf=8 Rb=10)



2N5551 / MMBT5551





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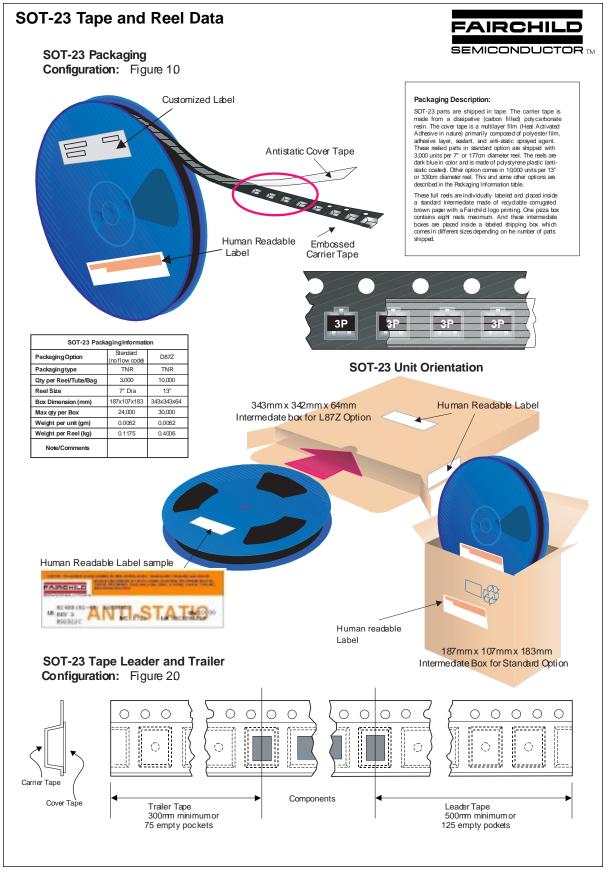
March 2001, Rev. B1





July 1999, Rev. A



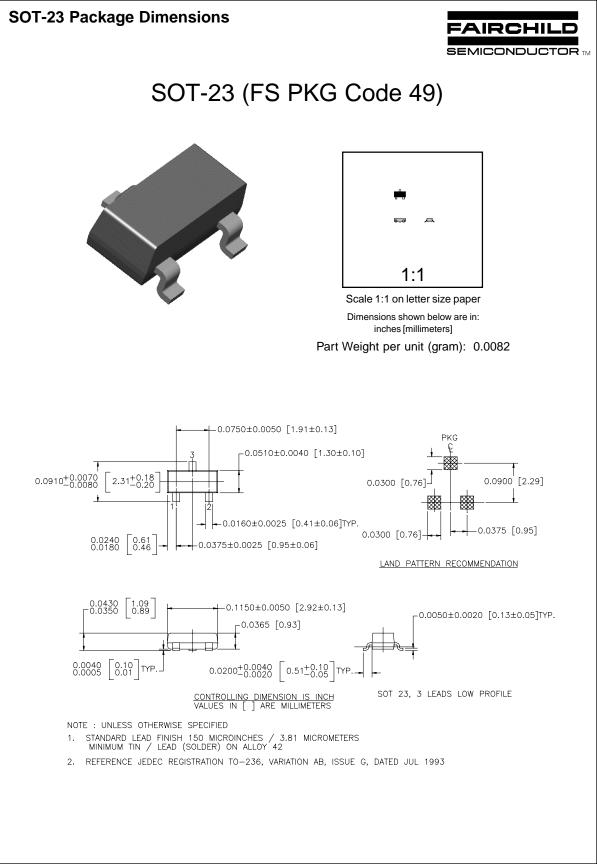


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